

OA1180
Gold Bonded Germanium Diode

FEATURES

Low forward voltage drop—low power consumption
Thirty years of proven reliability—one million hours mean time between failures (MTBF)
Very low noise level
Metallurgically bonded

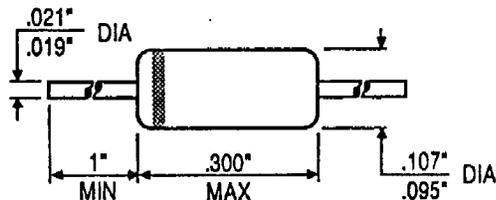
ABSOLUTE MAXIMUM RATINGS (at 25 °C, unless otherwise specified)

Peak Inverse Voltage 30 Volts
Peak Forward Current 500 mA
Operating Temperature - 65 °C to 85 °C
Average Power Dissipation 80 mW

ELECTRICAL CHARACTERISTICS

	Symbol	Conditions	Min	Max	Unit	T °C
Peak Inverse Voltage	PIV	1 mA	30		V	25 °C
Reverse Current	I_r	10 V		20	μ A	25 °C
Forward Voltage	V_f	100 mA		0.75	V	25 °C

MECHANICAL



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